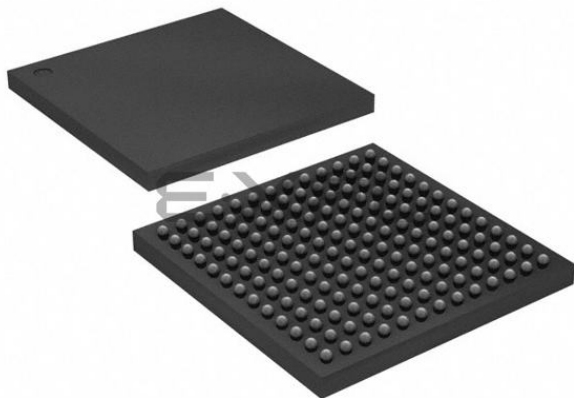




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	130
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	169-UFBGA
Supplier Device Package	169-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f427aih6

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The DMA can be used with the main peripherals:

- SPI and I²S
- I²C
- USART
- General-purpose, basic and advanced-control timers TIMx
- DAC
- SDIO
- Camera interface (DCMI)
- ADC
- SAI1.

3.9 Flexible memory controller (FMC)

All devices embed an FMC. It has four Chip Select outputs supporting the following modes: PCCard/Compact Flash, SDRAM/LPDDR SDRAM, SRAM, PSRAM, NOR Flash and NAND Flash.

Functionality overview:

- 8-, 16-, 32-bit data bus width
- Read FIFO for SDRAM controller
- Write FIFO
- Maximum FMC_CLK/FMC_SDCLK frequency for synchronous accesses is 90 MHz.

LCD parallel interface

The FMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

3.10 LCD-TFT controller (available only on STM32F429xx)

The LCD-TFT display controller provides a 24-bit parallel digital RGB (Red, Green, Blue) and delivers all signals to interface directly to a broad range of LCD and TFT panels up to XGA (1024x768) resolution with the following features:

- 2 displays layers with dedicated FIFO (64x32-bit)
- Color Look-Up table (CLUT) up to 256 colors (256x24-bit) per layer
- Up to 8 Input color formats selectable per layer
- Flexible blending between two layers using alpha value (per pixel or constant)
- Flexible programmable parameters for each layer
- Color keying (transparency color)
- Up to 4 programmable interrupt events.

Additional 32-bit registers contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the V_{BAT} pin.

3.20 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled.

The voltage regulator can be put either in main regulator mode (MR) or in low-power mode (LPR). Both modes can be configured as follows (see [Table 5: Voltage regulator modes in stop mode](#)):

- Normal mode (default mode when MR or LPR is enabled)
- Under-drive mode.

The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup).

Table 5. Voltage regulator modes in stop mode

Voltage regulator configuration	Main regulator (MR)	Low-power regulator (LPR)
Normal mode	MR ON	LPR ON
Under-drive mode	MR in under-drive mode	LPR in under-drive mode

- **Standby mode**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

The standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

Table 6. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary output	Max interface clock (MHz)	Max timer clock (MHz) ⁽¹⁾
Advanced -control	TIM1, TIM8	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	Yes	90	180
General purpose	TIM2, TIM5	32-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	45	90/180
	TIM3, TIM4	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	45	90/180
	TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No	90	180
	TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No	90	180
	TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No	45	90/180
	TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No	45	90/180
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No	45	90/180

1. The maximum timer clock is either 90 or 180 MHz depending on TIMPRE bit configuration in the RCC_DCKCFGR register.

3.30 Secure digital input/output interface (SDIO)

An SD/SDIO/MMC host interface is available, that supports MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

The interface allows data transfer at up to 48 MHz, and is compliant with the SD Memory Card Specification Version 2.0.

The SDIO Card Specification Version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDIO/MMC4.2 card at any one time and a stack of MMC4.1 or previous.

In addition to SD/SDIO/MMC, this interface is fully compliant with the CE-ATA digital protocol Rev1.1.

3.31 Ethernet MAC interface with dedicated DMA and IEEE 1588 support

The devices provide an IEEE-802.3-2002-compliant media access controller (MAC) for ethernet LAN communications through an industry-standard medium-independent interface (MII) or a reduced medium-independent interface (RMII). The microcontroller requires an external physical interface device (PHY) to connect to the physical LAN bus (twisted-pair, fiber, etc.). The PHY is connected to the device MII port using 17 signals for MII or 9 signals for RMII, and can be clocked using the 25 MHz (MII) from the microcontroller.

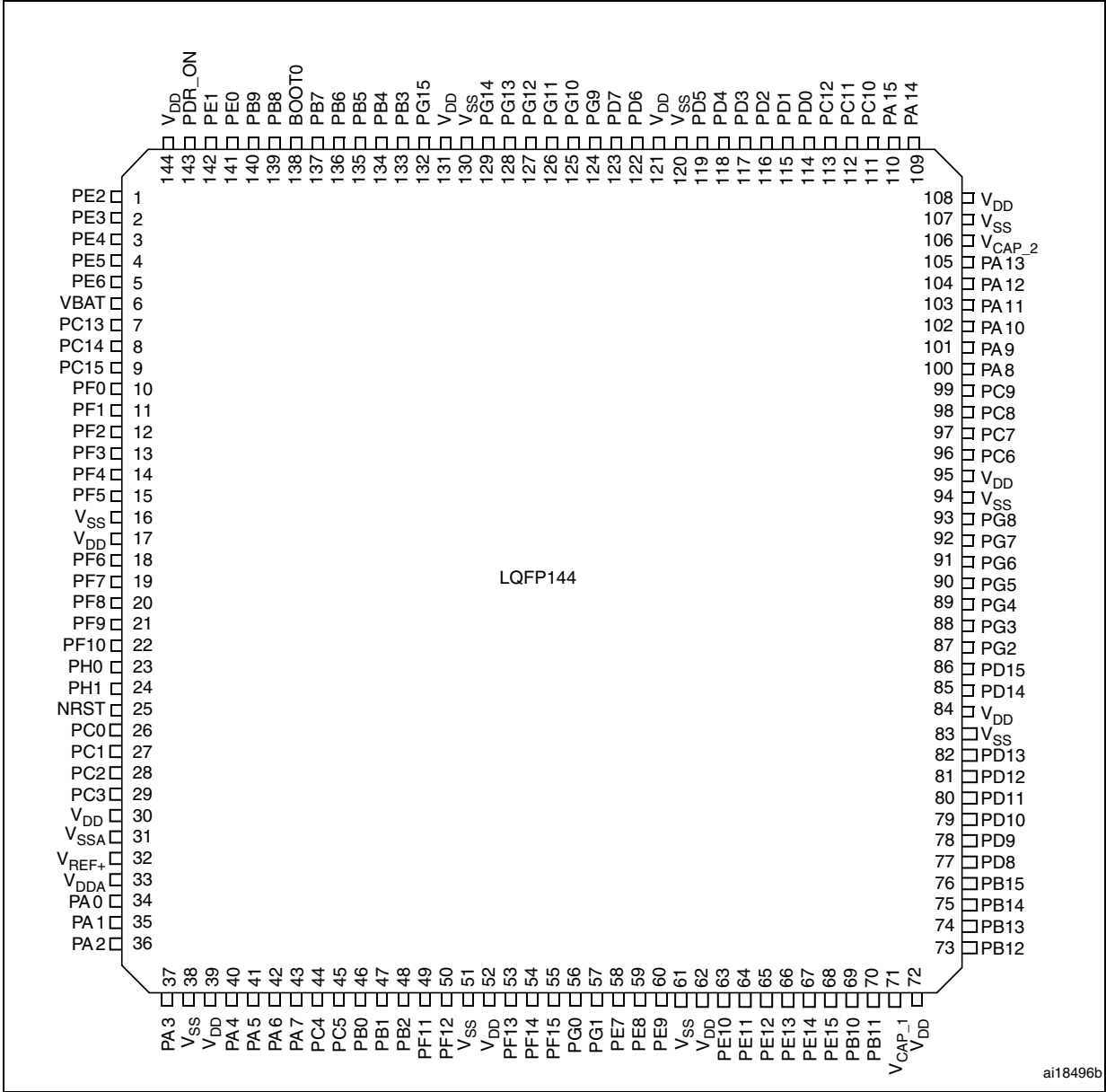
The devices include the following features:

- Supports 10 and 100 Mbit/s rates
- Dedicated DMA controller allowing high-speed transfers between the dedicated SRAM and the descriptors (see the STM32F4xx reference manual for details)
- Tagged MAC frame support (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- MAC control sublayer (control frames) support
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes.
- Supports hardware PTP (precision time protocol) in accordance with IEEE 1588 2008 (PTP V2) with the time stamp comparator connected to the TIM2 input
- Triggers interrupt when system time becomes greater than target time

3.32 Controller area network (bxCAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bitrate up to 1 Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive

Figure 13. STM32F42x LQFP144 pinout



1. The above figure shows the package top view.

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number								Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
22	33	J4	R1	39	L10	42	R1	V _{DDA}	S	-	-	-	-
23	34	J5	N3	40	K9	43	N3	PA0-WKUP (PA0)	I/O	FT	(6)	TIM2_CH1/TIM2_ETR, TIM5_CH1, TIM8_ETR, USART2_CTS, UART4_TX, ETH_MII_CRD, EVENTOUT	ADC123_ IN0/WKUP (5)
24	35	K1	N2	41	K8	44	N2	PA1	I/O	FT	(5)	TIM2_CH2, TIM5_CH2, USART2_RTS, UART4_RX, ETH_MII_RX_CLK/ETH _RMII_REF_CLK, EVENTOUT	ADC123_ IN1
25	36	K2	P2	42	L9	45	P2	PA2	I/O	FT	(5)	TIM2_CH3, TIM5_CH3, TIM9_CH1, USART2_TX, ETH_MDIO, EVENTOUT	ADC123_ IN2
-	-	L2	F4	43	-	46	K4	PH2	I/O	FT	-	ETH_MII_CRD, FMC_SDCKE0, LCD_R0, EVENTOUT	-
-	-	L1	G4	44	-	47	J4	PH3	I/O	FT	-	ETH_MII_COL, FMC_SDNE0, LCD_R1, EVENTOUT	-
-	-	M2	H4	45	-	48	H4	PH4	I/O	FT	-	I2C2_SCL, OTG_HS_ULPI_NXT, EVENTOUT	-
-	-	L3	J4	46	-	49	J3	PH5	I/O	FT	-	I2C2_SDA, SPI5_NSS, FMC_SDNWE, EVENTOUT	-
26	37	K3	R2	47	M11	50	R2	PA3	I/O	FT	(5)	TIM2_CH4, TIM5_CH4, TIM9_CH2, USART2_RX, OTG_HS_ULPI_D0, ETH_MII_COL, LCD_B5, EVENTOUT	ADC123_ IN3
27	38	-	-	-	-	51	K6	V _{SS}	S	-	-	-	-

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number								Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
58	80	H10	N14	99	K2	111	N10	PD11	I/O	FT	-	USART3_CTS, FMC_A16, EVENTOUT	-
59	81	J13	N13	100	H6	112	M10	PD12	I/O	FT	-	TIM4_CH1, USART3_RTS, FMC_A17, EVENTOUT	-
60	82	K12	M15	101	H5	113	M11	PD13	I/O	FT	-	TIM4_CH2, FMC_A18, EVENTOUT	-
-	83	-	-	102	-	114	J10	V _{SS}	S		-	-	-
-	84	F7	J13	103	L1	115	J11	V _{DD}	S		-	-	-
61	85	H11	M14	104	J2	116	L12	PD14	I/O	FT	-	TIM4_CH3, FMC_D0, EVENTOUT	-
62	86	J12	L14	105	K1	117	K13	PD15	I/O	FT	-	TIM4_CH4, FMC_D1, EVENTOUT	-
-	-	-	-	-	-	118	K12	PJ6	I/O	FT	-	LCD_R7, EVENTOUT	-
-	-	-	-	-	-	119	J12	PJ7	I/O	FT	-	LCD_G0, EVENTOUT	-
-	-	-	-	-	-	120	H12	PJ8	I/O	FT	-	LCD_G1, EVENTOUT	-
-	-	-	-	-	-	121	J13	PJ9	I/O	FT	-	LCD_G2, EVENTOUT	-
-	-	-	-	-	-	122	H13	PJ10	I/O	FT	-	LCD_G3, EVENTOUT	-
-	-	-	-	-	-	123	G12	PJ11	I/O	FT	-	LCD_G4, EVENTOUT	-
-	-	-	-	-	-	124	H11	VDD	I/O	FT	-	-	-
-	-	-	-	-	-	125	H10	VSS	I/O	FT	-	-	-
-	-	-	-	-	-	126	G13	PK0	I/O	FT	-	LCD_G5, EVENTOUT	-
-	-	-	-	-	-	127	F12	PK1	I/O	FT	-	LCD_G6, EVENTOUT	-
-	-	-	-	-	-	128	F13	PK2	I/O	FT	-	LCD_G7, EVENTOUT	-
-	87	H13	L15	106	J1	129	M13	PG2	I/O	FT	-	FMC_A12, EVENTOUT	-
-	88	NC (2)	K15	107	G3	130	M12	PG3	I/O	FT	-	FMC_A13, EVENTOUT	-
-	89	H12	K14	108	G5	131	N12	PG4	I/O	FT	-	FMC_A14/FMC_BA0, EVENTOUT	-
-	90	G13	K13	109	G6	132	N11	PG5	I/O	FT	-	FMC_A15/FMC_BA1, EVENTOUT	-

Table 22. reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{RUSH}^{(1)}$	InRush current on voltage regulator power-on (POR or wakeup from Standby)		-	160	200	mA
$E_{RUSH}^{(1)}$	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	$V_{DD} = 1.7\text{ V}$, $T_A = 105\text{ }^{\circ}\text{C}$, $I_{RUSH} = 171\text{ mA}$ for $31\text{ }\mu\text{s}$	-	-	5.4	μC

1. Guaranteed by design.
2. The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

6.3.6 Over-drive switching characteristics

When the over-drive mode switches from enabled to disabled or disabled to enabled, the system clock is stalled during the internal voltage set-up.

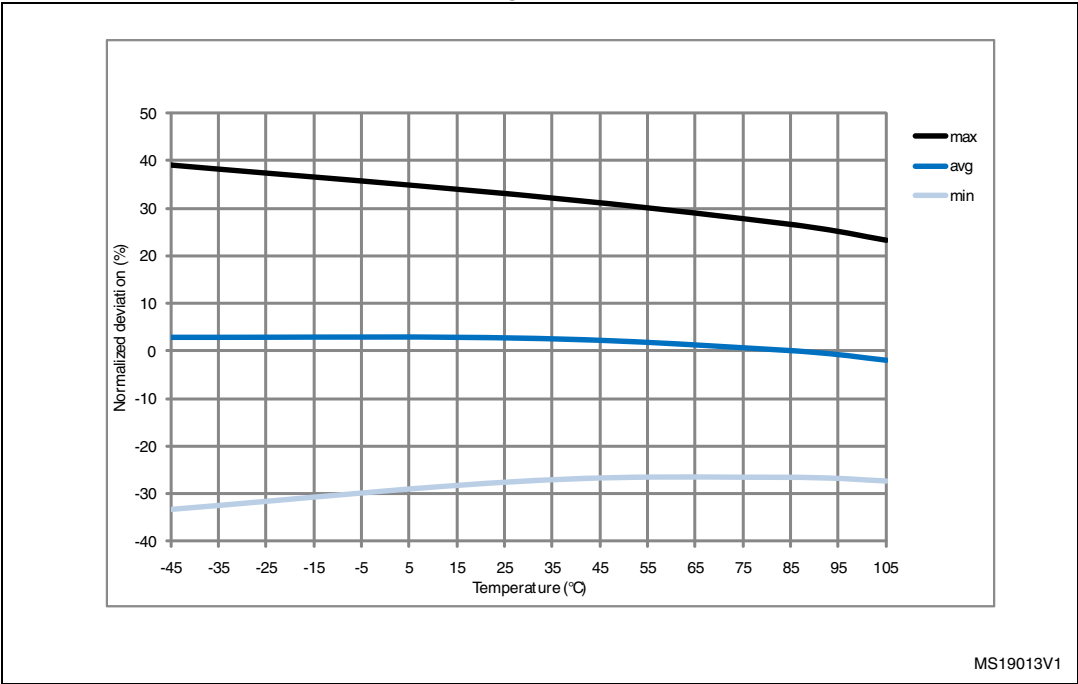
The over-drive switching characteristics are given in [Table 23](#). They are subject to general operating conditions for T_A .

Table 23. Over-drive switching characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Tod_swen	Over_drive switch enable time	HSI	-	45	-	μs
		HSE max for 4 MHz and min for 26 MHz	45	-	100	
		External HSE 50 MHz	-	40	-	
Tod_swdis	Over_drive switch disable time	HSI	-	20	-	
		HSE max for 4 MHz and min for 26 MHz.	20	-	80	
		External HSE 50 MHz	-	15	-	

1. Guaranteed by design.

Figure 32. ACC_{LSI} versus temperature



6.3.11 PLL characteristics

The parameters given in [Table 43](#) and [Table 44](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

Table 43. Main PLL characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{PLL_IN}	PLL input clock ⁽¹⁾		0.95 ⁽²⁾	1	2.10	MHz
f _{PLL_OUT}	PLL multiplier output clock		24	-	180	MHz
f _{PLL48_OUT}	48 MHz PLL multiplier output clock		-	48	75	MHz
f _{VCO_OUT}	PLL VCO output		100	-	432	MHz
t _{LOCK}	PLL lock time	VCO freq = 100 MHz	75	-	200	μs
		VCO freq = 432 MHz	100	-	300	

6.3.15 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/ESDA/JEDEC JS-001 and ANSI/ESD S5.3.1 standards.

Table 53. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
$V_{\text{ESD(HBM)}}$	Electrostatic discharge voltage (human body model)	$T_A = +25\text{ °C}$ conforming to ANSI/ESDA/JEDEC JS-001	2	2000	V
$V_{\text{ESD(CDM)}}$	Electrostatic discharge voltage (charge device model)	$T_A = +25\text{ °C}$ conforming to ANSI/ESD S5.3.1, LQFP100/144/176, UFBGA169/176, TFBGA176 and WLCSP143 packages	C3	250	
		$T_A = +25\text{ °C}$ conforming to ANSI/ESD S5.3.1, LQFP208 package	C3	250	

1. Guaranteed by characterization results.

Static latchup

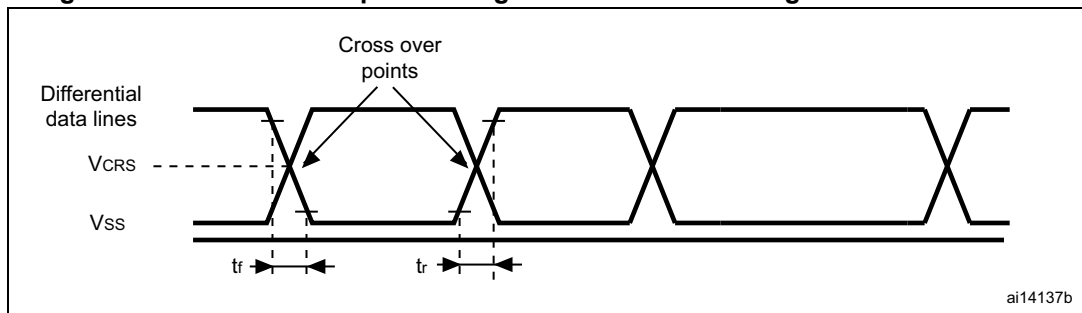
Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 54. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ °C}$ conforming to JESD78A	II level A

Figure 45. USB OTG full speed timings: definition of data signal rise and fall time**Table 67. USB OTG full speed electrical characteristics⁽¹⁾**

Driver characteristics					
Symbol	Parameter	Conditions	Min	Max	Unit
t_r	Rise time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_f	Fall time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V
Z_{DRV}	Output driver impedance ⁽³⁾	Driving high or low	28	44	Ω

1. Guaranteed by design.

2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

3. No external termination series resistors are required on DP (D+) and DM (D-) pins since the matching impedance is included in the embedded driver.

USB high speed (HS) characteristics

Unless otherwise specified, the parameters given in [Table 70](#) for ULPI are derived from tests performed under the ambient temperature, f_{HCLK} frequency summarized in [Table 69](#) and V_{DD} supply voltage conditions summarized in [Table 68](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$, unless otherwise specified
- Capacitive load $C = 30 \text{ pF}$, unless otherwise specified
- Measurement points are done at CMOS levels: $0.5V_{DD}$.

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

Table 68. USB HS DC electrical characteristics

Symbol		Parameter	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input level	V_{DD}	USB OTG HS operating voltage	1.7	3.6	V

1. All the voltages are measured from the local ground potential.

Table 86. Asynchronous non-multiplexed SRAM/PSRAM/NOR - read timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{h(Data_NOE)}$	Data hold time after FMC_NOE high	0	-	ns
$t_{h(Data_NE)}$	Data hold time after FMC_NEx high	0	-	ns
$t_{v(NADV_NE)}$	FMC_NEx low to FMC_NADV low	-	0	ns
$t_{w(NADV)}$	FMC_NADV low time	-	$T_{HCLK} + 1$	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization results.

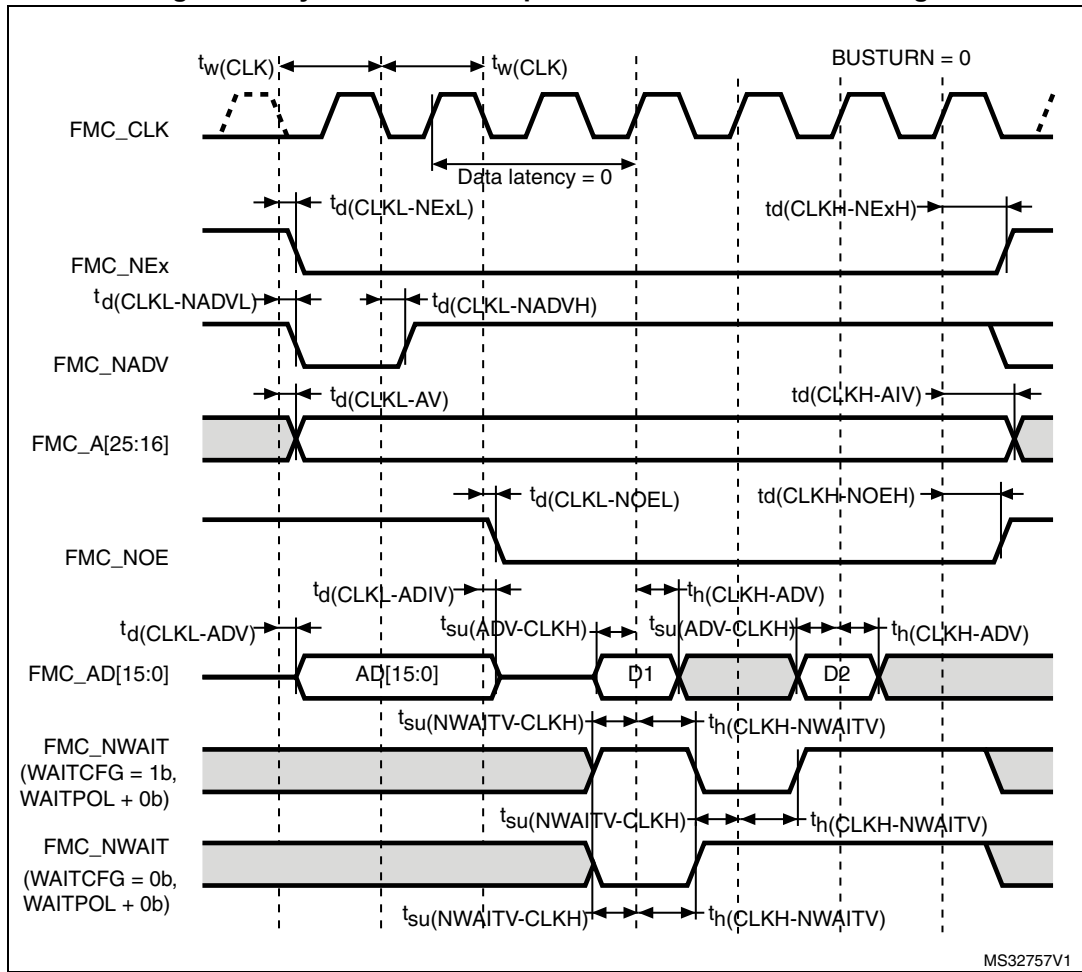
Table 87. Asynchronous non-multiplexed SRAM/PSRAM/NOR read - NWAIT timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$7T_{HCLK} + 0.5$	$7T_{HCLK} + 1$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK} - 1.5$	$5T_{HCLK} + 2$	
$t_{su(NWAIT_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK} + 1.5$	-	
$t_{h(NE_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK} + 1$	-	

1. $C_L = 30$ pF.

2. Guaranteed by characterization results.

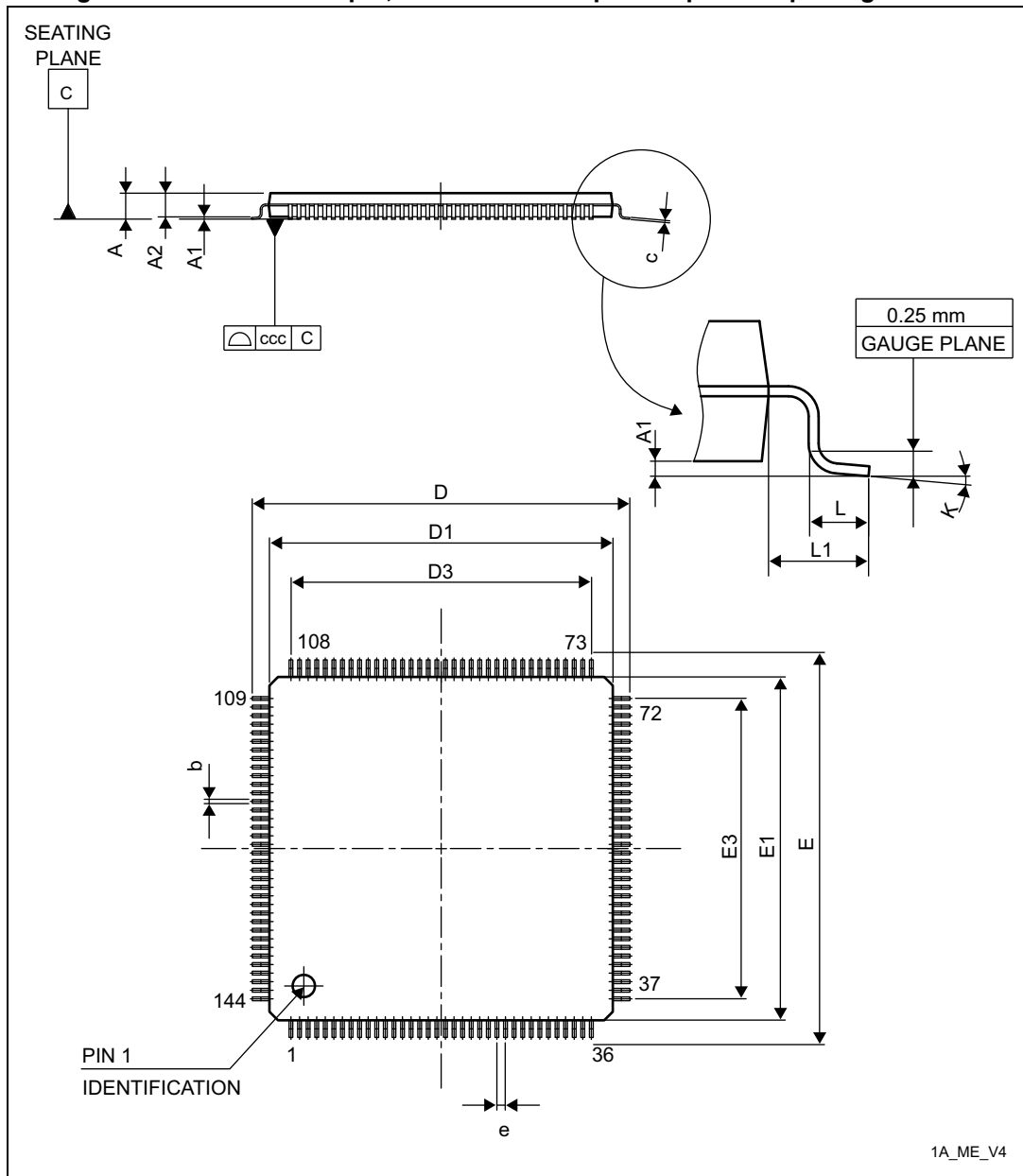
Figure 59. Synchronous multiplexed NOR/PSRAM read timings

Table 94. Synchronous multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK} - 1$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	0	ns
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x=0..2)	T_{HCLK}	-	ns
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	0	ns
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	ns
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16...25)	-	0	ns
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16...25)	0	-	ns
$t_{d(CLKL-NOEL)}$	FMC_CLK low to FMC_NOE low	-	$T_{HCLK} + 0.5$	ns
$t_{d(CLKH-NOEH)}$	FMC_CLK high to FMC_NOE high	$T_{HCLK} - 0.5$	-	ns
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	0.5	ns
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	ns

7.3 LQFP144 package information

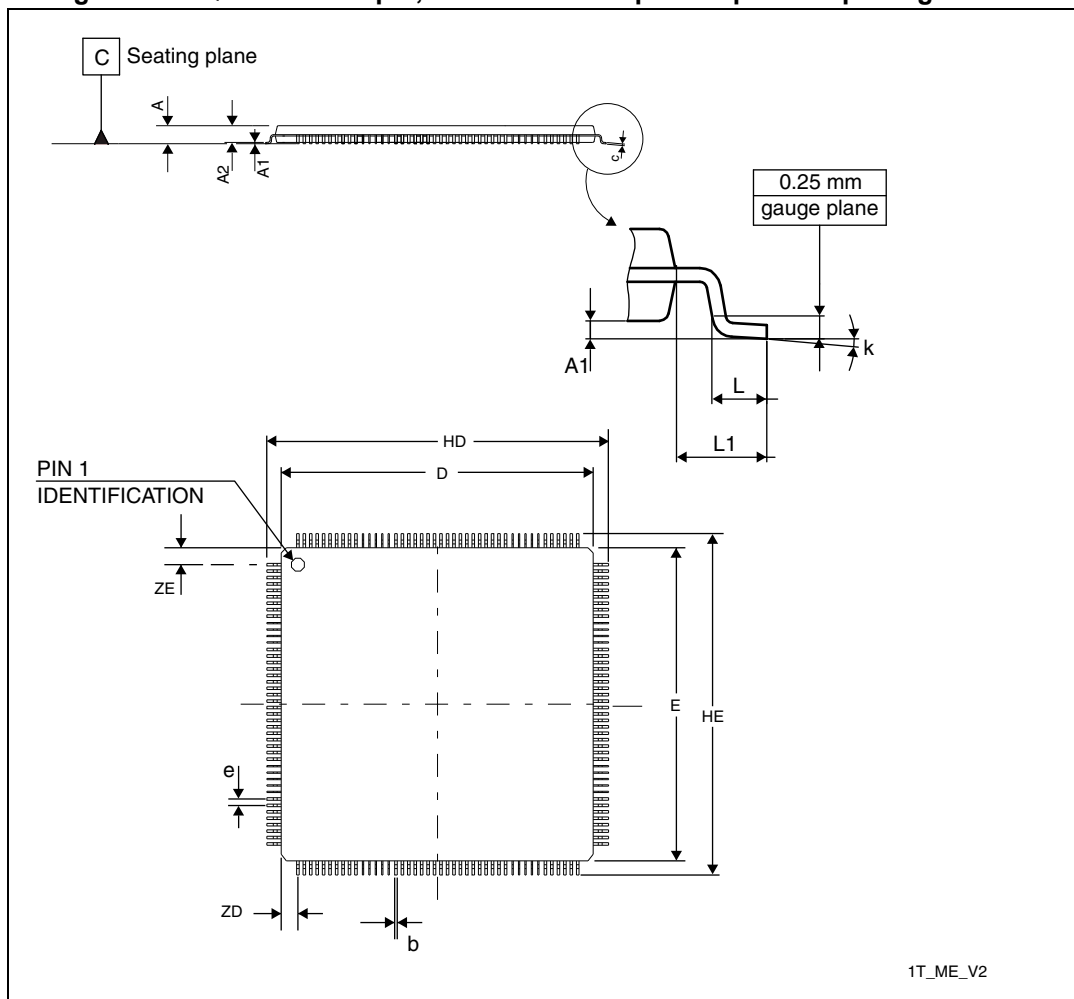
Figure 86. LQFP144-144-pin, 20 x 20 mm low-profile quad flat package outline



1. Drawing is not to scale.

7.4 LQFP176 package information

Figure 89. LQFP176 - 176-pin, 24 x 24 mm low-profile quad flat package outline



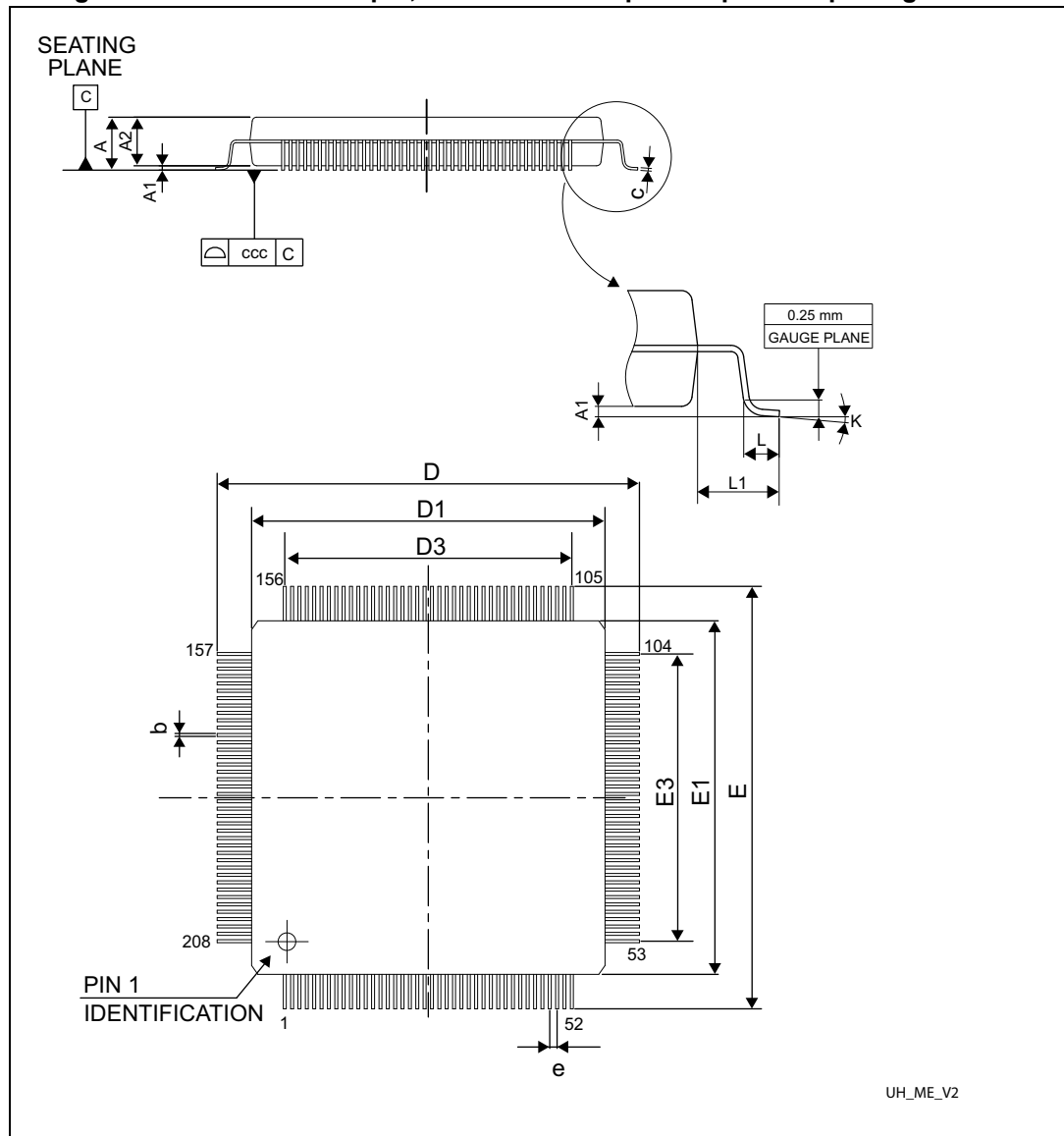
1. Drawing is not to scale.

Table 114. LQFP176 - 176-pin, 24 x 24 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	-	1.450	0.0531	-	0.0571
b	0.170	-	0.270	0.0067	-	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	23.900	-	24.100	0.9409	-	0.9488
HD	25.900	-	26.100	1.0197	-	1.0276

7.5 LQFP208 package information

Figure 92. LQFP208 - 208-pin, 28 x 28 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 115. LQFP208 - 208-pin, 28 x 28 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	--	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	29.800	30.000	30.200	1.1732	1.1811	1.1890
D1	27.800	28.000	28.200	1.0945	1.1024	1.1102
D3	-	25.500	-	-	1.0039	-
E	29.800	30.000	30.200	1.1732	1.1811	1.1890
E1	27.800	28.000	28.200	1.0945	1.1024	1.1102
E3	-	25.500	-	-	1.0039	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7.0°	0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

7.9 Thermal characteristics

The maximum chip-junction temperature, $T_J \text{ max}$, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- $T_A \text{ max}$ is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- $P_D \text{ max}$ is the sum of $P_{INT} \text{ max}$ and $P_{I/O} \text{ max}$ ($P_D \text{ max} = P_{INT} \text{ max} + P_{I/O} \text{ max}$),
- $P_{INT} \text{ max}$ is the product of I_{DD} and V_{DD} , expressed in Watts. This is the maximum chip internal power.

$P_{I/O} \text{ max}$ represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma (V_{DD} - V_{OH}) \times I_{OH},$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 121. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch	43	°C/W
	Thermal resistance junction-ambient WLCSP143	31.2	
	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient LQFP176 - 24 × 24 mm / 0.5 mm pitch	38	
	Thermal resistance junction-ambient LQFP208 - 28 × 28 mm / 0.5 mm pitch	19	
	Thermal resistance junction-ambient UFBGA169 - 7 × 7mm / 0.5 mm pitch	52	
	Thermal resistance junction-ambient UFBGA176 - 10 × 10 mm / 0.5 mm pitch	39	
	Thermal resistance junction-ambient TFBGA216 - 13 × 13 mm / 0.8 mm pitch	29	

Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.